

**NTE2366**  
**Silicon PNP Transistor**  
**High Voltage Video Amp**  
**(Compl to NTE399)**

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

|   |                |
|---|----------------|
| Collector–Base Voltage, $V_{CBO}$ .....     | 300V           |
| Collector–Emitter Voltage, $V_{CEO}$ .....  | 300V           |
| Emitter–Base Voltage, $V_{EBO}$ .....       | 5V             |
| Collector Current, $I_C$                    |                |
| Continuous .....                            | 100mA          |
| Peak .....                                  | 200mA          |
| Power Dissipation, $P_C$ .....              | 1.0W           |
| Operating Junction Temperature, $T_j$ ..... | +150°C         |
| Storage Temperature Range, $T_{stg}$ .....  | -55° to +150°C |

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

| Parameter                            | Symbol        | Test Conditions                       | Min | Typ | Max | Unit          |
|--------------------------------------|---------------|---------------------------------------|-----|-----|-----|---------------|
| Collector Cutoff Current             | $I_{CBO}$     | $V_{CB} = 200V, I_E = 0$              | –   | –   | 0.1 | $\mu\text{A}$ |
| Emitter Cutoff Current               | $I_{EBO}$     | $V_{EB} = 4V, I_C = 0$                | –   | –   | 0.1 | $\mu\text{A}$ |
| Collector–Base Breakdown Voltage     | $V_{(BR)CBO}$ | $I_C = 10\mu\text{A}, I_E = 0$        | 300 | –   | –   | V             |
| Collector–Emitter Breakdown Voltage  | $V_{(BR)CEO}$ | $I_C = 1\text{mA}, R_{BE} = \infty$   | 300 | –   | –   | V             |
| Emitter–Base Breakdown Voltage       | $V_{(BR)EBO}$ | $I_E = 10\mu\text{A}, I_C = 0$        | 5   | –   | –   | V             |
| DC Current Gain                      | $h_{FE}$      | $V_{CE} = 10V, I_C = 10\text{mA}$     | 40  | –   | 320 |               |
| Collector–Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 20\text{mA}, I_B = 2\text{mA}$ | –   | –   | 0.6 | V             |
| Base–Emitter Saturation Voltage      | $V_{BE(sat)}$ | $I_C = 20\text{mA}, I_B = 2\text{mA}$ | –   | –   | 1.0 | V             |
| Current Gain–Bandwidth Product       | $f_T$         | $V_{CE} = 30V, I_C = 10\text{mA}$     | –   | 150 | –   | MHz           |
| Capacitance                          | $C_{ob}$      | $V_{CB} = 30V, f = 1\text{MHz}$       | –   | 2.6 | –   | pF            |
| Reverse Transfer Capacitance         | $C_{re}$      | $V_{CB} = 30V, f = 1\text{MHz}$       | –   | 1.8 | –   | pF            |

